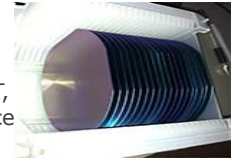




Silicon Crystal & Compound Semiconductor

↘ FZ Single Crystal Silicon Wafer

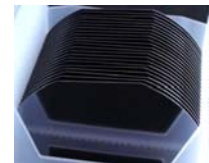
FZ Single Crystal Silicon Wafer, introducing vertical floating zone refining technology, allowing a lower resistivity variation, fewer Oxygen, Carbon or Nitrogen contamination, but much higher surface mechanical strength, which has widely been used for electronic devices fabrication such as, power rectifier, thyristor, GTO, MOSFET, IGBT, etc. P-type or N-type conductivity with as-cut, lapped, etched or polished surface finish is available. 2" 3" 4" 5" and 6" can be supplied.



No.	Items	Standard Specifications				
1	Size	2"	3"	4"	5"	6"
2	Diameter mm	50.8	76.2	100	125	150
3	Conductivity	P/N	P/N	P/N	P/N	P/N
4	Orientation	<100>, <110>, <111>				
5	Thickness μm	180, 279, 381, 425, 525, 575, 675 or as required				
6	Resistivity $\Omega\cdot\text{cm}$	10-20, 40-60, 800-1000, 1000-1400 or as required				
7	RRV max	25%	25%	25%	25%	25%
8	TTV $\mu\text{m max}$	10	10	10	10	10
9	Bow/Warp $\mu\text{m max}$	30	30	30	30	30
10	Carbon Content $\text{a/cm}^3 \text{ max}$	5E16	5E16	5E16	5E16	5E16
11	Oxygen Content $\text{a/cm}^3 \text{ max}$	1E18	1E18	1E18	1E18	1E18
12	Surface Finish	As-cut, L/L, P/E, P/P etc				
13	Packing	Foam box or cassette inside, carton box outside				

↘ FZ NTD Single Crystal Silicon Wafer

FZ NTD (Neutron Transmutation Doping) Single Crystal Silicon Wafer is of advantages including high doping accuracy, high uniformity, small axial and radial resistivity variation, lower impurity or compensation of group III-V elements, therefore, being widely used for electronic devices fabrication such as, power rectifier, thyristor, GTO, MOSFET, IGBT etc. N-type conductivity with as-cut or lapped surface finish is available, 2" 3" 4" 5" and 6" can be supplied.



No.	Items	Standard Specifications				
1	Size	2"	3"	4"	5"	6"
2	Diameter	50.8	76.2	100	125	150
3	Conductivity	N	N	N	N	N
4	Orientation	<100>, <111>				
5	Thickness μm	180, 279, 381, 425, 525, 575, 625, 675 or as required				
6	Resistivity $\Omega\cdot\text{cm}$	36-44, 44-52, 90-110, 100-250, 200-400 or as required				
7	RRV max	8%, 10%, 12% or as required				
8	TTV $\mu\text{m max}$	10	10	10	10	10
9	Bow/Warp $\mu\text{m max}$	30	30	30	30	30
10	Carbon Content $\text{a/cm}^3 \text{ max}$	5E16	5E16	5E16	5E16	5E16
11	Oxygen Content $\text{a/cm}^3 \text{ max}$	1E18	1E18	1E18	1E18	1E18
12	Carrier Lifetime $\mu\text{s min}$	200, 300, 400, 500, 600, 800, 1000 or as required				
13	Surface Finish	As-cut or Lapped				
14	Packing	Foam box inside, carton box outside				

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